



System Design for mainstream TLC SSD

Meeting the performance challenge

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Forward-Looking Statements

During our meeting today we may make forward-looking statements.

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Agenda

- **MLC, TLC Raw NAND comparison**
- **TLC NAND Attributes and Challenges**
- **TLC SSD: Bridging the Performance Gap with MLC SSDs**
- **Optimal use of DRAM**
- **NAND Parallelism for optimal performance**
- **Tiered Storage Approach**
- **The SLC advantage**
- **Writes to TLC**
 - **Direct**
 - **TLC writes via SLC**
- **Further performance improvement techniques**
- **Knobs to fine tune cost vs. performance**
- **Performance Comparison**
- **Conclusion**



MLC, TLC Raw NAND comparison

Metrics	2 Bit Per Cell (MLC) 1ynm 64Gb/128Gb *	3 Bit Per Cell (TLC) 1ynm 64Gb/128Gb **
Read (Page)	45 us	80 us (Lower Page)
		105 us (Middle Page)
		80 us (Upper Page)
Program (Page)	1350 us	550 us (First Cycle)
		1700 us (Second cycle)
		4650 us (Third Cycle)
Erase (Block)	4 ms	10 ms

* SanDisk 1Ynm 128 Gb eX3 datasheet

** SanDisk 1Ynm 64 Gb eX2 datasheet

SLC: Single level cell

MLC: Multi level cell

TLC: Three level cell

TLC NAND Attributes and Challenges



Cost
Density (small FF)



Reliability
Endurance
Performance

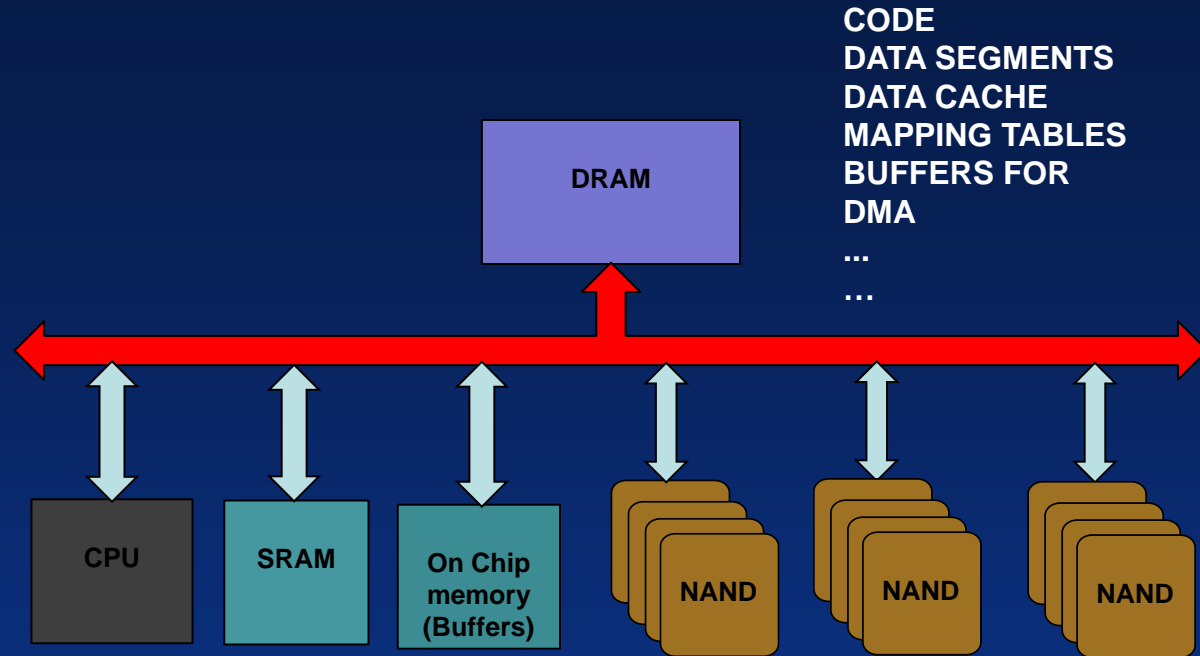
How to Make a competitive TLC SSD for cost-sensitive mainstream market?



Bridging the Performance Gap with MLC SSDs

Optimal use of DRAM

**DRAM access
can become the
bottleneck.**



**What can
be done?**

Control structures

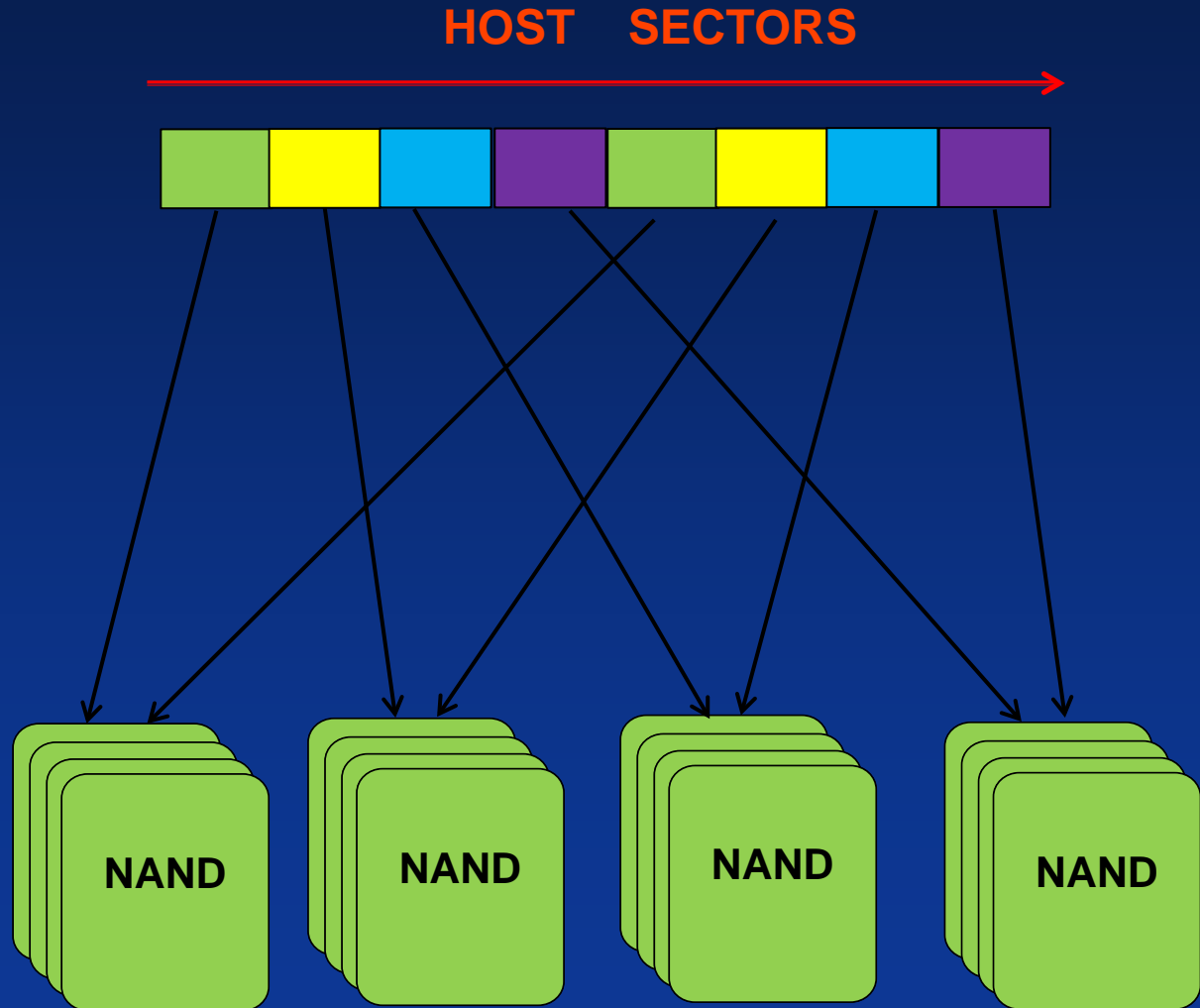
- Align to Cache boundary (Cached access)

Data Cache

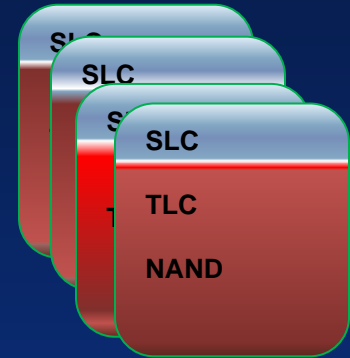
- Cache implementation for Quick lookup
 - Algorithm to determine optimal caching benefit
 - Sequential read stream - Read look ahead
- Sequential Write stream - Bypass cache

NAND Parallelism for optimal performance

- Multiple Parallel Flash Channels enough to saturate Front End Interface bandwidth.
- Map host sector range for optimal use of multiple flash devices



Use part of TLC Blocks as SLC



Comparison Metrics	TLC 1ynm 128Gb *	
	SLC mode	TLC mode
Read (page)	50 us	80 us (Lower Page)
		105us (Middle Page)
		80 us (Upper Page)
Program (page)	350 us	550 us (First Cycle)
		1700 us (Second cycle)
		4650 us (Third Cycle)
Erase (block)	10 ms	10 ms

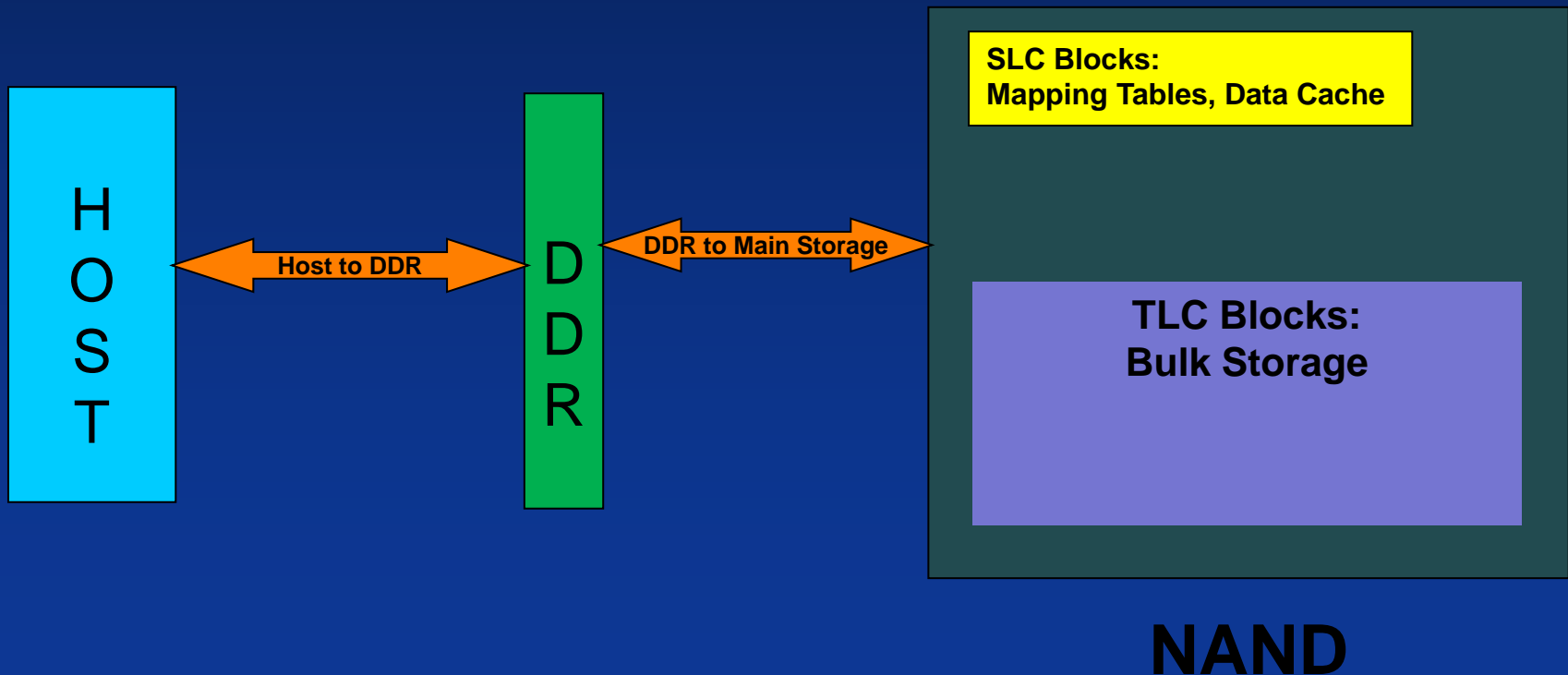
- **SLC block size is 1/3 of TLC**
- **Reduced Capacity**

* SanDisk 1Ynm 128 Gb eX3 datasheet

- * **Faster access time of SLC**
- * **Higher Program / Erase cycles**

Tiered Storage Approach

SLC: control structures, data cache,
TLC : Bulk Storage





The SLC advantage

Mapping Tables in SLC

- Speeds up drive boot and shutdown time
- Shorter wake up time from Dev Sleep
- Faster mapping table updates
- More table updates possible during drive's life

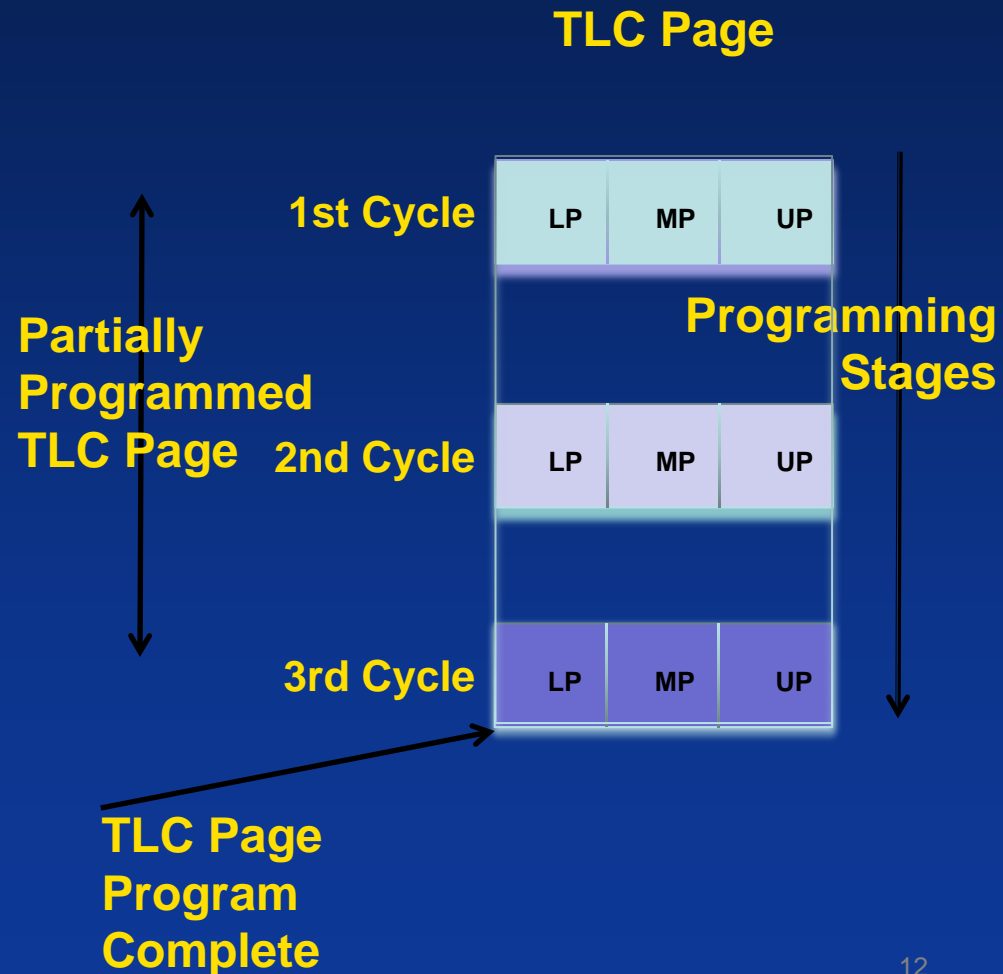
SLC as Data Cache

- Fast completion of most host IOs

Writes to TLC Blocks

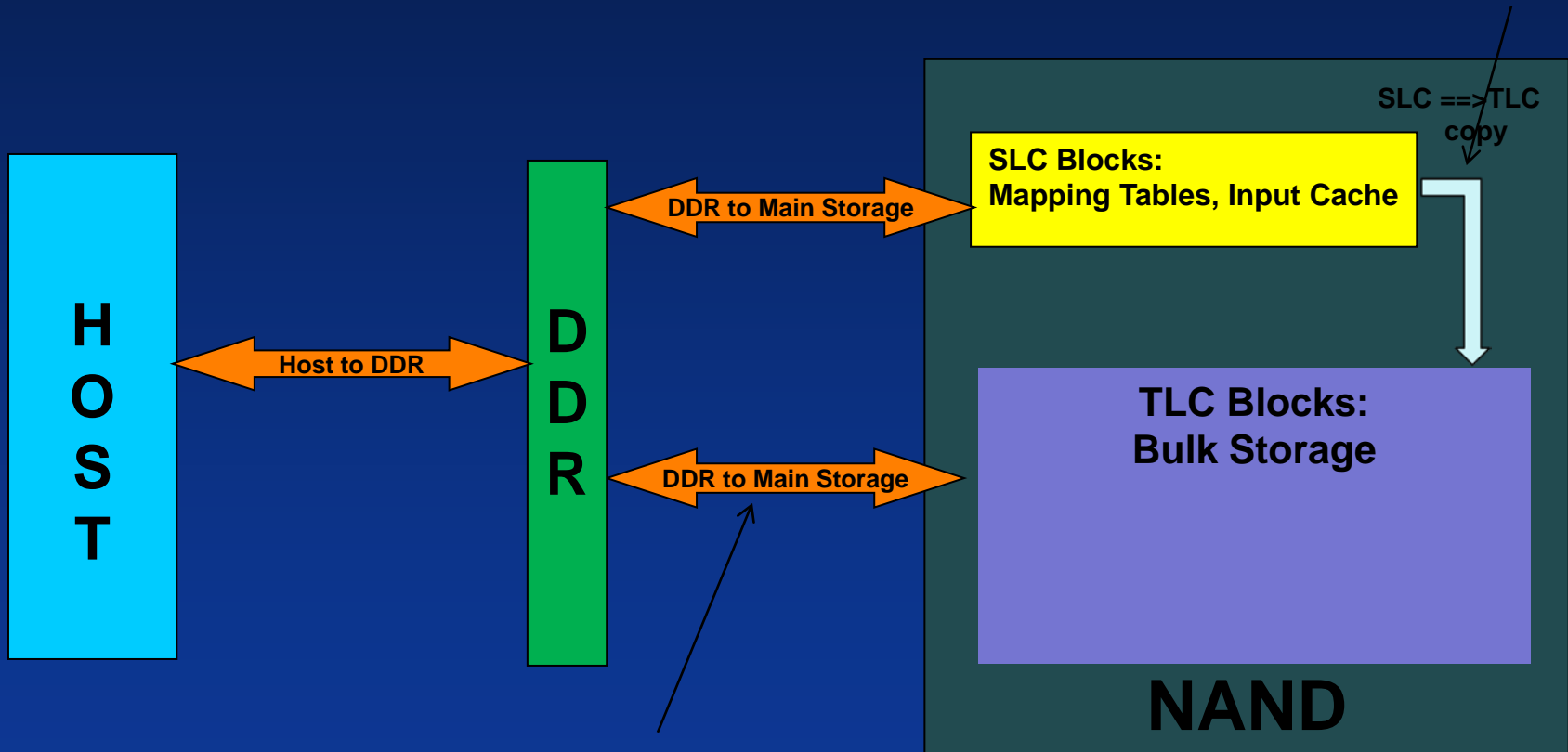
TLC writes

- Multiple steps in TLC page programming
- Expensive (slow) operations



Writes to TLC Blocks: Options

TLC Writes Via SLC



Direct TLC Writes



Direct host data write to TLC blocks

Host data is directly programmed to TLC blocks from DDR buffer

- No intermediate writes
- Lower Write Amplification
- Higher sustained sequential write performance

- TLC program sequence requires buffering multiple pages.
 - More DRAM requirement for buffers
- Some pages are not readable during programming
- Higher Flush Command response time
- System Complexity

TLC writes via SLC

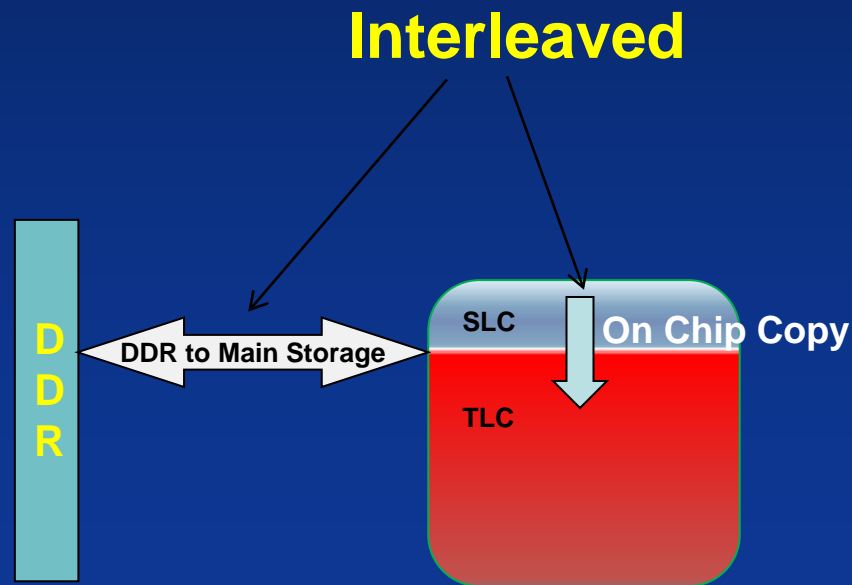
2 Stages

- Write host data first to SLC
- Copy data from SLC to TLC

- High Burst write performance
- TLC writes are mostly background activity.
- No additional DDR requirement
- No penalty for read operations
- Lower sustained Sequential write performance
- Higher WA as data is rewritten
- Possible Silent error build up during Copy

Further performance improvement techniques

- Plane interleaving using multi-plane operations
- Cached access to SLC & TLC
- Interleave NAND bus interface and internal NAND operations during On-Chip-Copy



Knobs to fine tune cost vs. performance



Larger SLC block pool

- Keep most of the host program traffic operations satisfied from SLC pool
- TLC writes occur mostly during background activity.

Capacity Loss

TLC block overprovisioning

- Reduced need to free (erase) blocks
- More NAND bandwidth for host traffic

Capacity Loss



SATA 6Gb/s MLC and TLC SDD performance comparison*

Parameter	Unit	Queue Depth	480 / 512 GB MLC SSD **	480 / 512 GB TLC SSD***
Sequential Read	MB/s	32	520	At Par
Sequential Write	MB/s	32	460	At Par
Random Read[4KB]	IOPS	1	8,500	At Par
		32	96,000	At Par
Random Write[4KB]	IOPS	1	19,000	At Par
		32	80,000	At Par
Read / Write Latency	Us	1	55/65	At Par
OFF to ON Resume Time	Ms	N/A	690	At Par
PCMark (Secondary)	IOPS		75K	At Par

CrystalDiskMark
on Win7 platform

Secondary drive

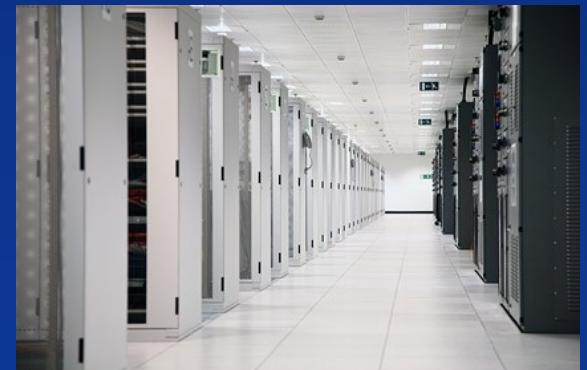
- * SanDisk Internal Test
- ** SanDisk X300s
- *** Sample TLC SSD

Conclusion

Mainstream SSD market is cost-sensitive. It demands storage capacity, reliability and performance at lower price.



TLC SSD meets the middle ground on metrics for mainstream client SSD and price sensitive segments of enterprise (hyper scale) storage markets.





Thank You!

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